

Contents

1	Introduction to Low Power Issues in VLSI — 1
1.1	Introduction to VLSI — 1
1.2	Low Power IC Design beyond Sub-20 nm Technology — 2
1.3	Issues Related to Silicon Manufacturability and Variation — 3
1.4	Issues Related to Design Productivity — 4
1.5	Limitation Faced by CMOS — 4
1.6	International Technology Roadmap for Semiconductors — 5
1.7	Different Groups of MOSFETs — 8
1.8	Three MOS Types — 9
1.9	Low Leakage MOSFET — 9
1.10	Importance of Subthreshold Slope — 10
1.11	Why Is Subthreshold Current Exponential in Nature? — 13
1.12	Subthreshold Leakage and Voltage Limits — 15
1.13	Importance of Subthreshold Slope in Low Power Operation — 16
1.14	Ultralow Voltage Operation — 16
1.15	Low Power Analog Circuit Design — 17
1.16	Fundamental Consequence of Lowering Supply Voltage — 18
1.17	Analog MOS Transistor Performance Parameters — 19
	Summary — 21
	References — 22
2	Scaling and Short Channel Effects in MOSFET — 24
2.1	MOSFET Scaling — 24
2.2	International Technology Roadmap for Semiconductors — 24
2.3	Gate Oxide Scaling — 25
2.4	Gate Leakage Current — 25
2.5	Mobility — 26
2.6	High- k Gate Dielectrics — 26
2.7	Key Guidelines for Selecting an Alternative Gate Dielectric — 26
2.8	Materials — 26
2.9	Gate Tunneling Current — 27
2.10	Gate Length Scaling — 27
2.11	Introduction to Short Channel Effect in MOSFET — 27
2.11.1	Reduction of Effective Threshold Voltage — 28
2.11.2	Drain-induced Barrier Lowering — 28
2.11.3	Mobility Degradation and Surface Scattering — 30
2.11.4	Surface Scattering — 32
2.11.5	Hot Carrier Effect — 32
2.11.6	Punch-through Effect — 32
2.11.7	Velocity Saturation Effect — 32

2.11.8	Increase in Off-state Leakage Current —	34
2.12	Motivation for Present Research —	34
2.12.1	Lightly Doped Drain Structure —	35
2.12.2	Channel Engineering Technique —	36
2.12.3	Gate Engineering Technique —	37
2.12.4	Single Halo Dual Material Gate MOSFET —	37
2.12.5	Double Halo Dual Material Gate MOSFET —	38
2.12.6	Double Gate MOSFET —	38
2.12.7	Dual Material Double Gate MOSFET —	40
2.12.8	Triple Material Double Gate MOSFET —	41
2.12.9	FinFET —	41
2.12.10	Triple Gate MOSFET —	43
2.12.11	Gate-all-around MOSFET —	43
2.12.12	Surrounding Gate MOSFET —	43
2.12.13	Silicon Nanowires —	44
2.13	Fringing-induced Barrier Lowering —	45
2.14	Silicon-on-insulator MOSFETs —	45
2.15	Nonconventional Double Gate MOSFETs —	46
2.16	Tunnel Field-effect Transistor —	63
2.17	IMOS Device —	65
2.18	Summary —	65
	References —	66
3	Advanced Energy-reduced CMOS Inverter Design —	71
3.1	Introduction —	71
3.1.1	Transfer Characteristics of Inverter —	71
3.1.2	Static CMOS Inverter in Super-threshold Regime —	73
3.1.3	Introduction to Subthreshold Logic —	94
3.1.4	Summary —	107
	References —	108
4	Advanced Combinational Circuit Design —	112
	Introduction —	112
4.1	Static CMOS Logic Gate Design —	112
4.2	Complementary Properties of CMOS Logic —	112
4.2.1	CMOS NAND Gate —	113
4.2.2	CMOS NOR Gate —	113
4.2.3	Some More Examples of CMOS Logic —	115
4.2.4	XOR or Nonequivalence Gate Using CMOS Logic —	116
4.2.5	XOR–XNOR or Equivalence Gate Using CMOS Logic —	116
4.2.6	And-Or-Invert and Or-And-Invert Gates —	117
4.2.7	Full Adder Circuits Using CMOS Logic —	118
4.3	Pseudo-nMOS Gates —	120

4.3.1	Why the Name Is Pseudo-nMOS? — 123
4.3.2	Ratioed Logic — 123
4.3.3	Operation of Pseudo-nMOS Inverter — 124
4.4	Pass-transistor Logic — 125
4.5	Complementary Pass Transistor Logic — 127
4.6	Signal Restoring Pass Transistor Logic Design — 128
4.7	Sizing of Transistor in CMOS Design Style — 129
4.8	Introduction to Logical Effort — 132
4.8.1	Definitions of Logical Effort — 132
4.9	Delay Estimation by Logical Effort — 135
4.10	Introduction to Transmission Gate — 136
4.10.1	Use of CMOS TG as Switch — 138
4.10.2	2:1 Multiplexer Using TG — 141
4.10.3	XOR Gate Using TG — 141
4.10.4	XNOR Gate Using TG — 143
4.10.5	Transmission Gate Adders — 144
4.10.6	More Examples of TG Logic — 144
4.11	Tristate Buffer — 145
4.12	Transmission Gates and Tristates — 146
4.13	Implementation of Combinational Circuit Using DTMOS Logic for Ultralow Power Application — 149
4.14	ECLR Structure — 154
4.14.1	Power Consumption — 175
4.14.2	Propagation Delay — 175
	References — 175
5	Advanced Energy-reduced Sequential Circuit Design — 177
5.1	Introduction to Sequential Circuit — 177
5.2	Basics of Regenerative Circuits — 177
5.3	Basic SR Flip-flop/Latch — 181
5.3.1	NAND Gate-based Negative Logic SR Latch — 183
5.3.2	Clocked SR Latch — 183
5.4	Clocked JK Latch — 185
5.4.1	Toggle Switch — 186
5.5	Master-slave Flip-flop — 186
5.6	D Latch — 187
5.6.1	Positive and Negative Latch — 188
5.6.2	Multiplexer-based Latch — 188
5.7	Master-slave Edge-triggered Flip-flops — 190
5.8	Timing Parameters for Sequential Circuits — 192
5.8.1	Timing of Multiplexer-based Master-slave Flip- flop — 194

5.8.2	The Sizing Requirements for the Transmission Gates — 195
5.9	Clock Skews due to Nonideal Clock Signal — 196
5.10	Design and Analysis of the Flip-flops Using DTMOS Style — 197
5.10.1	<i>SR</i> Latch and Flip-flop — 197
5.10.2	<i>JK</i> Latch and <i>JK</i> Flip-flop — 201
5.10.3	<i>D</i> Flip-flop — 202
5.11	Adiabatic Flip-flop — 205
	References — 207
6	Introduction to Memory Design — 208
	Introduction — 208
6.1	Types of Semiconductor Memory — 208
6.2	Memory Organization — 210
6.3	Introduction to DRAM — 212
6.4	One-transistor DRAM Cell — 213
6.4.1	Write — 214
6.4.2	Hold — 214
6.4.3	Read — 215
6.5	Capacitor in DRAM — 217
6.6	Refresh Operation of DRAM — 219
6.7	DRAM Types — 220
6.7.1	FPM DRAMs — 220
6.7.2	Extended Data Out DRAMs — 221
6.7.3	Burst EDO DRAMs — 221
6.7.4	ARAM — 221
6.7.5	Cache DRAM — 221
6.7.6	Enhanced DRAM (EDRAM) — 221
6.7.7	Synchronous DRAM — 222
6.7.8	Double Data Read DRAMs — 222
6.7.9	Synchronous Graphic RAM — 222
6.7.10	Enhanced Synchronous DRAMs — 222
6.7.11	Video DRAMs — 223
6.7.12	Window DRAMs — 223
6.7.13	Pseudo-static RAMs — 223
6.7.14	Rambus DRAMs — 223
6.7.15	Multibank DRAM — 224
6.7.16	Ferroelectric DRAM — 224
6.8	SOI DRAM — 225
6.8.1	Operating Principle — 225
6.8.2	Design Considerations of SOI DRAM — 226
6.9	Introduction to SRAM — 226

6.10	SRAM Cell and Its Operation — 227
6.11	SRAM Cell Failures — 228
6.12	Performance Metrics of SRAM — 228
6.12.1	Static Noise Margin — 228
6.12.2	Reliability Issues of 6-T SRAM — 229
6.13	Read-only Memory — 230
6.14	EPROM — 233
6.15	Electrically Erasable Programmable Read-only Memory (E ² PROM) — 234
6.16	Flash Memory — 236
6.17	Summary — 238
	References — 239
7	Analog Low Power VLSI Circuit Design — 242
7.1	Analog Low Power Design: Problems with Transistor Mismatch — 242
7.2	Mixed-signal Design with Sub-100 nm Technology — 243
7.3	Challenges in MS Design in Sub-100 nm Space — 244
7.3.1	Lack of Convergence of Technology — 244
7.3.2	Digital Scaling — 245
7.3.3	Memory Scaling — 246
7.3.4	Analog Scaling — 247
7.3.5	Degraded SNR — 247
7.3.6	Degradation in Intrinsic Gain — 248
7.3.7	Device Leakage — 248
7.3.8	Mismatch due to Reduced Matching — 248
7.3.9	Availability of Models — 248
7.3.10	Passives — 248
7.3.11	RF Scaling — 249
7.3.12	Issues Related with Power Devices — 250
7.4	Basics of Switched-capacitor Circuits — 250
7.4.1	Resistor Emulation Using SC Network — 251
7.4.2	Integrator Using SC Circuits — 252
7.4.3	SC Integrator Sensitive to Parasitic — 255
7.4.4	Low Power Switched-capacitor Circuit — 256
7.5	Current Source/Sink — 258
7.5.1	Technique to Increase Output Resistance — 261
7.6	Low Power Current Mirror — 263
7.6.1	Use of Current Mirrors in IC — 263
7.6.2	Simple Current Mirror — 265
7.6.3	Wilson Current Mirror — 267
7.6.4	Cascode Current Mirror — 268
7.6.5	Low Voltage Current Mirror — 270
7.7	Fundamentals of Current/Voltage Reference — 273

7.7.1	Another Way to Obtain Simple Bootstrap Voltage Reference Circuit with Start-up Circuit —	279
7.8	Bandgap Voltage Reference —	282
7.8.1	Positive TC Voltage —	282
7.8.2	Negative TC Voltage —	283
7.9	An Introduction to Analog Design Automation —	284
7.9.1	Survey of Previous Analog Design Flow —	285
7.9.2	Analog and Mixed-signal Design Process —	288
7.9.3	Hierarchical Analog Design Methodology —	290
7.9.4	Current Status for the Main Tasks in Analog Design Automation —	292
7.10	Field-programmable Analog Arrays —	299
7.11	Summary —	301
	References —	301

Index —	305
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